

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

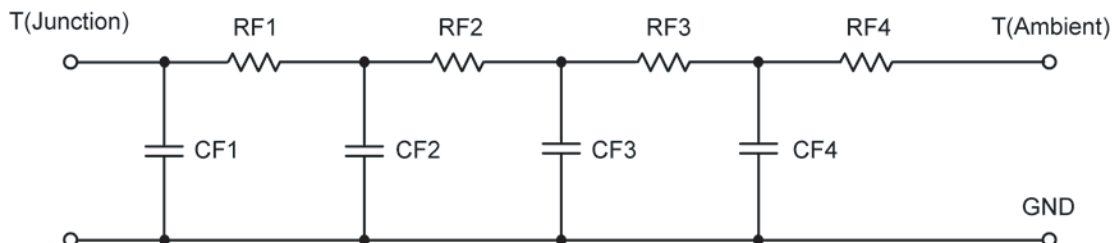
*For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	8.2097	N/A	5.9095
RT2	5.6187	N/A	1.1458
RT3	25.3777	N/A	2.1362
RT4	45.7939	N/A	12.8085
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	903.8016 m	N/A	11.8245 m
CT2	4.5883 m	N/A	2.6354 m
CT3	39.4360 m	N/A	38.7429 m
CT4	1.3741	N/A	91.9240 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	8.7780	N/A	1.2921
RF2	28.1670	N/A	8.1662
RF3	34.0994	N/A	5.8190
RF4	13.9556	N/A	6.7227
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	5.4213 m	N/A	1.5249 m
CF2	38.4831 m	N/A	6.3236 m
CF3	968.9754 m	N/A	40.8340 m
CF4	2.2971	N/A	138.9300 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

